

SPECIALIST DETECTORS FOR NUCLEAR PHYSICS

SILICON DETECTOR TYPE:	TOTALLY DEPLETED SINGLE SIDED MICROSTRIP
DESIGN:	Silicon planar ion implanted passivated structure p on n silicon totally depleted single sided microstrip design exhibiting over voltage depletion capability with excellent radiation damage resistance and annealing capability for high neutron and heavy ion damage levels.
ACTIVE AREA:	20 x 20 mm ²
ACTIVE LENGTH:	20 mm
ELEMENT PITCH:	2 mm
ACTIVE WIDTH:	20 mm
N ^o of CHANNELS:	10
N ^o of READOUTS:	100 %
THICKNESS:	200 μm, 300 μm, 450 μm and 600 μm
OPERATING VOLTAGE:	100 + 50 V
LEAKAGE CURRENT:	10 nA
RISE TIME:	10 ns /100 μm
ELEMENT CAPACITANCE:	8 – 24 pF
CONTACTING METALLISATION:	Aluminum 3000 – 8000 Å
PACKAGE:	PCB with single sided readout Dimensions – 35 x 34 mm ²

QUALITY ASSURANCE :ISO9001

